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November 2013



SGH40N60UF 600 V PT IGBT

General Description

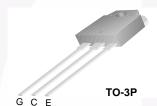
Fairchild's UF series IGBTs provide low conduction and switching losses. UF series is designed for the applications such as general inverter and PFC where high speed switching is required feature.

Features

- · High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.1 V @ I_C = 20 A
- High Input Impedance

Application

General Inverter, PFC





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	$@ T_C = 25^{\circ}C$	40	А
IC	Collector Current	@ T _C = 100°C	20	Α
I _{CM (1)}	Pulsed Collector Current		160	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	160	W
	Maximum Power Dissipation	@ T _C = 100°C	64	W
T _J	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes:
(1) Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.77	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Chai	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \text{ uA}$	600			V
ΔB _{VCES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 100	nA
On Char	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 20 \text{ mA}, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
•	Collector to Emitter	$I_C = 20 \text{ A}, V_{GF} = 15 \text{ V}$		2.1	2.6	V
V _{CE(sat)}	Saturation Voltage	I _C = 40 A, V _{GE} = 15 V		2.6		V
Dvnami	c Characteristics					
C _{ies}	Input Capacitance	V _{CE} = 30 V, V _{GE} = 0 V,		1430		pF
ries				170		pF
	Output Capacitance					
C _{oes}	Output Capacitance Reverse Transfer Capacitance	f = 1 MHz		50		•
C _{oes} C _{res} Switchir	Reverse Transfer Capacitance ng Characteristics			50		pF
C _{oes} C _{res} Switchir	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time			50		pF
$\frac{C_{oes}}{C_{res}}$ Switchin $\frac{t_{d(on)}}{t_r}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time	f = 1 MHz	 	50 15 30		pF ns ns
$\frac{C_{oes}}{C_{res}}$ Switchin $\frac{t_{d(on)}}{t_r}$ $\frac{t_{d(off)}}{t_{d(off)}}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time	f = 1 MHz V _{CC} = 300 V, I _C = 20 A,	 	50 15 30 65	 130	ns ns ns
$\begin{aligned} & \frac{C_{oes}}{C_{res}} \\ & \frac{C_{res}}{Switchir} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(off)}}{t_f} \end{aligned}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$f = 1 \text{ MHz}$ $V_{CC} = 300 \text{ V, } I_{C} = 20 \text{ A,}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V,}$		50 15 30 65 50		pF ns ns ns
$\begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ \textbf{Switchir} \\ t_{d(on)} \\ t_{r} \\ \hline t_{d(off)} \\ t_{f} \\ E_{on} \\ \end{array}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	f = 1 MHz V _{CC} = 300 V, I _C = 20 A,	 	50 15 30 65 50 160	 130	ns ns ns ns
$\begin{aligned} & \frac{C_{oes}}{C_{res}} \\ & \frac{C_{res}}{Switchir} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(off)}}{t_f} \\ & \frac{E_{on}}{E_{off}} \end{aligned}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$f = 1 \text{ MHz}$ $V_{CC} = 300 \text{ V, } I_{C} = 20 \text{ A,}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V,}$	 	50 15 30 65 50 160 200	 130 150 	ns ns ns ns uJ
$ \begin{aligned} & C_{oes} \\ & C_{res} \end{aligned} $	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss	$f = 1 \text{ MHz}$ $V_{CC} = 300 \text{ V, } I_{C} = 20 \text{ A,}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V,}$	 	50 15 30 65 50 160 200 360	 130	ns ns ns ns uJ uJ
$\begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ \textbf{Switchir} \\ \hline \\ t_{d(on)} \\ t_r \\ \hline \\ t_{d(off)} \\ \hline \\ t_f \\ \hline \\ E_{on} \\ \hline \\ E_{off} \\ \hline \\ E_{ts} \\ \hline \\ t_{d(on)} \\ \hline \end{array}$	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time	$f = 1 \text{ MHz}$ $V_{CC} = 300 \text{ V, } I_{C} = 20 \text{ A,}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V,}$	 	50 15 30 65 50 160 200 360 30	 130 150 	ns ns ns ns uJ uJ uJ
$ \begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ Switchir \\ \hline t_{d(on)} \\ t_r \\ \hline t_{d(off)} \\ t_f \\ \hline E_{on} \\ \hline E_{off} \\ \hline E_{ts} \\ \hline t_{d(on)} \\ t_r \\ \hline \end{array} $	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	$f = 1 \text{ MHz}$ $V_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ Inductive Load, $T_{C} = 25^{\circ}\text{C}$	 	50 15 30 65 50 160 200 360 30 37	 130 150 600	ns ns ns ns uJ uJ uJ ns
$ \begin{aligned} & \frac{C_{oes}}{C_{res}} \\ & \frac{C_{res}}{Switchir} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(off)}}{t_f} \\ & \frac{E_{on}}{E_{ts}} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(off)}}{t_{d(off)}} \end{aligned} $	Reverse Transfer Capacitance ng Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time	$I_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$ $I_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$ $I_{CC} = 15 \text{ V},$ $I_{CC} = 1$	 	50 15 30 65 50 160 200 360 30 37 110	 130 150 600 200	ns ns ns uJ uJ ns ns ns
$ \begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ Switchir \\ \hline t_{d(on)} \\ t_r \\ \hline t_{d(off)} \\ \hline t_f \\ \hline E_{on} \\ \hline E_{off} \\ \hline E_{ts} \\ \hline t_{d(on)} \\ t_r \\ \hline t_{d(off)} \\ \hline t_r \\ \hline \end{array} $	Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time		 	50 15 30 65 50 160 200 360 30 37 110 144	 130 150 600	ns ns ns ns uJ uJ uJ ns
$ \begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ Switchir \\ \hline t_{d(on)} \\ t_r \\ \hline t_{d(off)} \\ t_f \\ \hline E_{on} \\ \hline E_{off} \\ \hline E_{ts} \\ \hline t_{d(on)} \\ t_r \\ \hline t_{d(off)} \\ t_r \\ \hline \\ \hline t_{d(off)} \\ \hline t_{f} \\ \hline \\ E_{on} \\ \hline \end{array} $	Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$I_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$ $I_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$ $I_{CC} = 15 \text{ V},$ $I_{CC} = 1$	 	50 15 30 65 50 160 200 360 30 37 110 144 310	 130 150 600 200 250	ns ns ns ns uJ uJ ns ns ns
$\begin{array}{l} C_{oes} \\ C_{res} \\ \end{array}$ $\begin{array}{l} \textbf{Switchir} \\ t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \\ \end{array}$ $\begin{array}{l} t_{d(off)} \\ t_{f} \\ \end{array}$ $\begin{array}{l} E_{on} \\ t_{d(on)} \\ t_{r} \\ \end{array}$ $\begin{array}{l} t_{d(off)} \\ t_{f} \\ \end{array}$	Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Turn-On Switching Loss			50 15 30 65 50 160 200 360 30 37 110 144 310 430	 130 150 600 200 250 	ns ns ns uJ uJ ns ns ns uJ
$ \begin{array}{l} C_{oes} \\ C_{res} \\ \hline \\ Switchir \\ t_{d(on)} \\ t_{r} \\ \hline \\ t_{d(off)} \\ t_{f} \\ \hline \\ E_{on} \\ \hline \\ E_{ts} \\ \hline \\ t_{d(on)} \\ t_{r} \\ \hline \\ t_{d(on)} \\ t_{r} \\ \hline \\ t_{d(off)} \\ t_{f} \\ \hline \\ E_{on} \\ \hline \\ E_{on} \\ \hline \\ E_{ts} \\ \hline \\ t_{d(off)} \\ t_{f} \\ \hline \\ E_{on} \\ \hline \\ E_{ts} \\ \hline \\ t_{d(off)} \\ t_{f} \\ \hline \\ E_{ts} \\ \hline \\ t_{d(off)} \\ t_{f} \\ \hline \\ E_{ts} \\ E_{ts} \\ \hline \\ E_{ts} \\ E_{$	Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Turn-On Switching Loss Turn-On Switching Loss Total Switching Loss	$f=1 \text{ MHz}$ $V_{CC}=300 \text{ V, } I_{C}=20 \text{ A,}$ $R_{G}=10 \Omega, V_{GE}=15 \text{ V,}$ $Inductive \text{ Load, } T_{C}=25^{\circ}\text{C}$ $V_{CC}=300 \text{ V, } I_{C}=20 \text{ A,}$ $R_{G}=10 \Omega, V_{GE}=15 \text{ V,}$ $Inductive \text{ Load, } T_{C}=125^{\circ}\text{C}$		50 15 30 65 50 160 200 360 30 37 110 144 310	 130 150 600 200 250	ns ns ns ns uJ uJ ns ns ns
$\begin{aligned} & \frac{C_{oes}}{C_{res}} \\ & \frac{C_{res}}{Switchir} \\ & \frac{t_{d(on)}}{t_r} \\ & \frac{t_{d(off)}}{t_f} \\ & \frac{E_{on}}{E_{off}} \\ & \frac{E_{ts}}{S} \end{aligned}$	Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-Off Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Turn-On Switching Loss			50 15 30 65 50 160 200 360 30 37 110 144 310 430 740	 130 150 600 200 250 1200	ns ns ns uJ uJ ns ns ns uJ

Measured 5mm from PKG

Internal Emitter Inductance

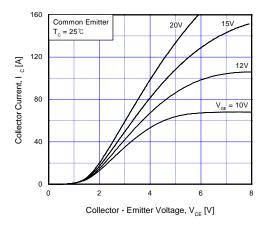


Fig 1. Typical Output Characteristics

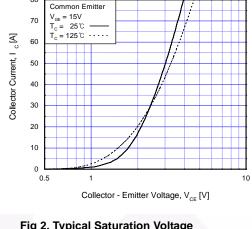


Fig 2. Typical Saturation Voltage Characteristics

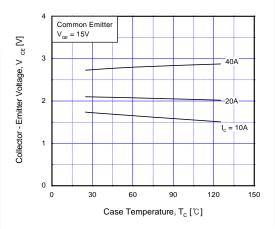


Fig 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

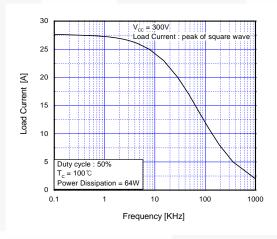


Fig 4. Load Current vs. Frequency

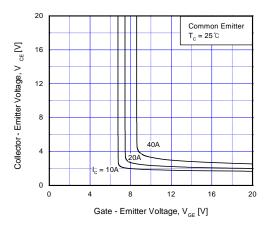


Fig 5. Saturation Voltage vs. V_{GE}

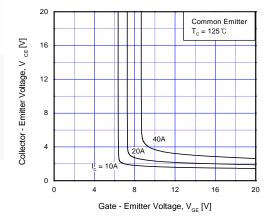


Fig 6. Saturation Voltage vs. $V_{\rm GE}$

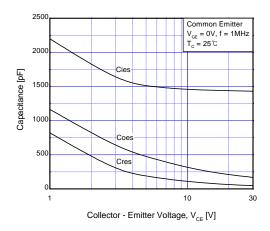


Fig 7. Capacitance Characteristics

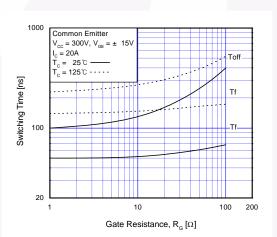


Fig 9. Turn-Off Characteristics vs.

Gate Resistance

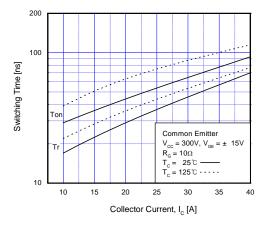


Fig 11. Turn-On Characteristics vs. Collector Current

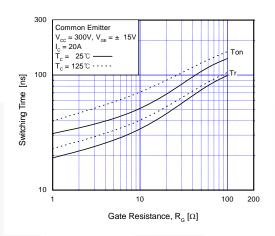


Fig 8. Turn-On Characteristics vs.
Gate Resistance

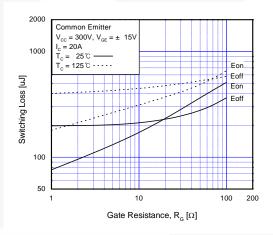


Fig 10. Switching Loss vs. Gate Resistance

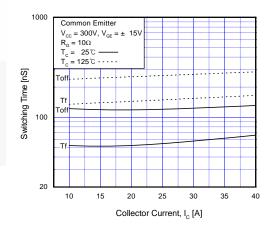


Fig 12. Turn-Off Characteristics vs. Collector Current

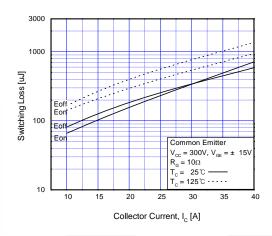


Fig 13. Switching Loss vs. Collector Current

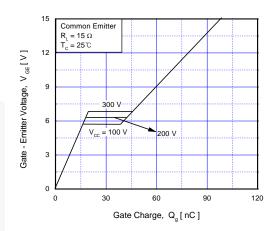


Fig 14. Gate Charge Characteristics

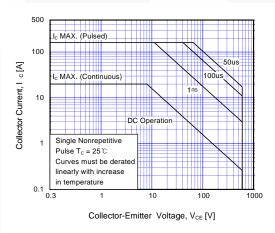


Fig 15. SOA Characteristics

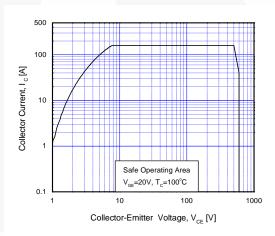


Fig 16. Turn-Off SOA Characteristics

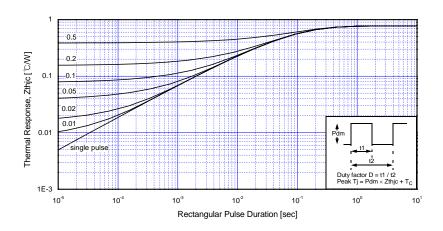


Fig 17. Transient Thermal Impedance of IGBT

Mechanical Dimensions

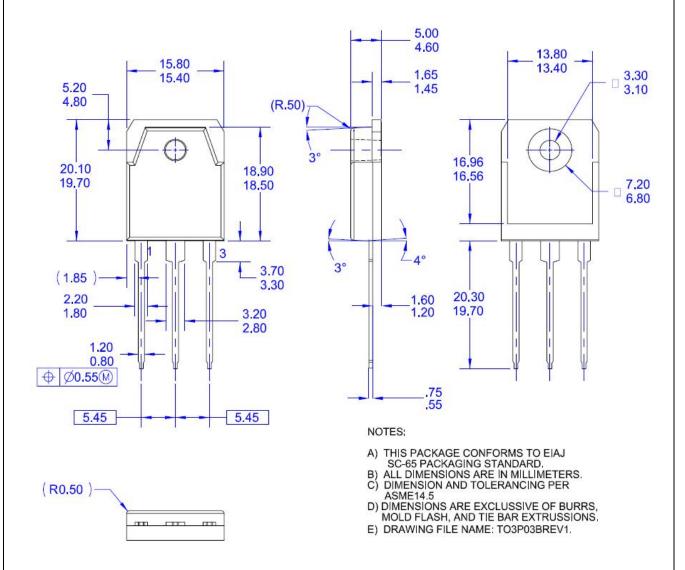


Figure 18. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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